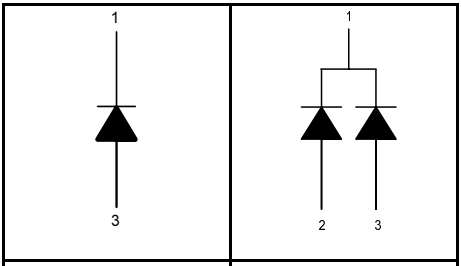
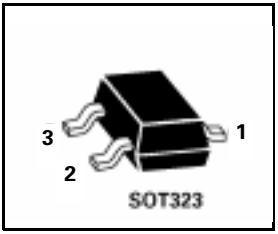
SOT323 SILICON EPITAXIAL SCHOTTKY BARRIER DIODES

ISSUE 1– DECEMBER 1998

ZUMD54
ZUMD54C





SINGLE	COMMON CATHODE
Device Type: ZUMD54	Device Type: ZUMD54C
Partmarking Detail: D8	Partmarking Detail: D8C

FEATURES: Low V_F & High Current Capability

APPLICATIONS: PSU, Mobile Telecomms & SCSI

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V_R	30	V
Forward Current	I_F	200	mA
Forward Voltage @ I_F =10mA	V_F	400	mV
Repetitive Peak Forward Current	I_{FRM}	300	mA
Non Repetitive Forward Current t<1s	I_{FSM}	600	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	330	mW
Storage Temperature Range	T_{stg}	-55 to +150	°C
JunctionTemperature ¤	T_j	125	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	$V_{(BR)R}$	30	50		V	I_R=10μA
Forward Voltage	V_F		135 200 280 350 530	240 320 400 500 1000	mV mV mV mV mV	I_F=0.1mA I_F=1mA I_F=10mA I_F=30mA I_F=100mA
Reverse Current	I_R		1.4	2	μA	V_R=25V
Diode Capacitance	C_D		7.5	10	pF	f=1MHz,V_R=1V
Reverse Recover Time	t_{rr}			5	ns	switched from I_F=10mA to I_R=10mA R_L=100Ω, Measured at I_R=1mA

ZUMD54
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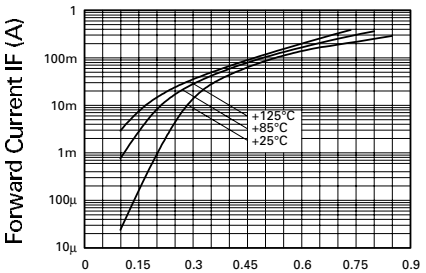
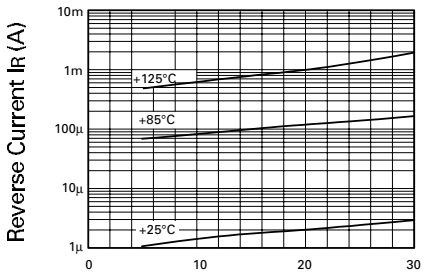
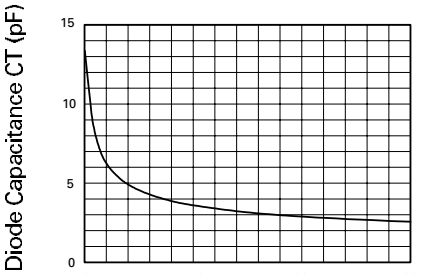
TYPICAL CHARACTERISTICS



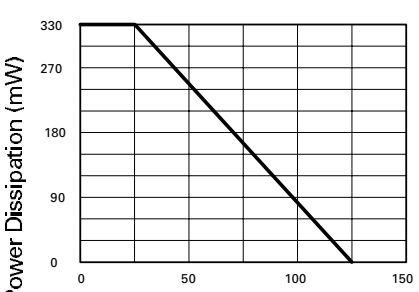
IF v VF Characteristics



IR v VR Characteristics



CT v VR Characteristics



PD v TA Characteristics